/ Descriptions

DFN1006-3L PNP

Silicon PNP transistor in a DFN1006-3L Plastic Package.

/ Features

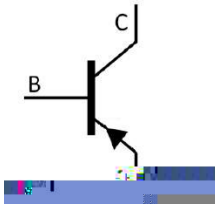
h_{FE} $V_{CE(sat)}$

High DC Current Gain, Low Collector to Emitter Saturation Voltage,HF product.

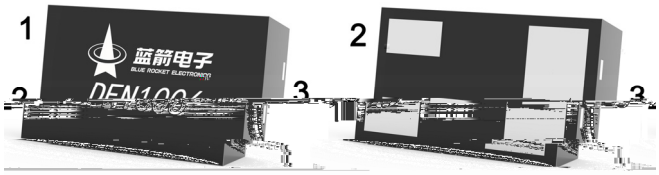
/ Applications

General purpose amplifier and switching.

/ Equivalent Circuit



/ Pinning

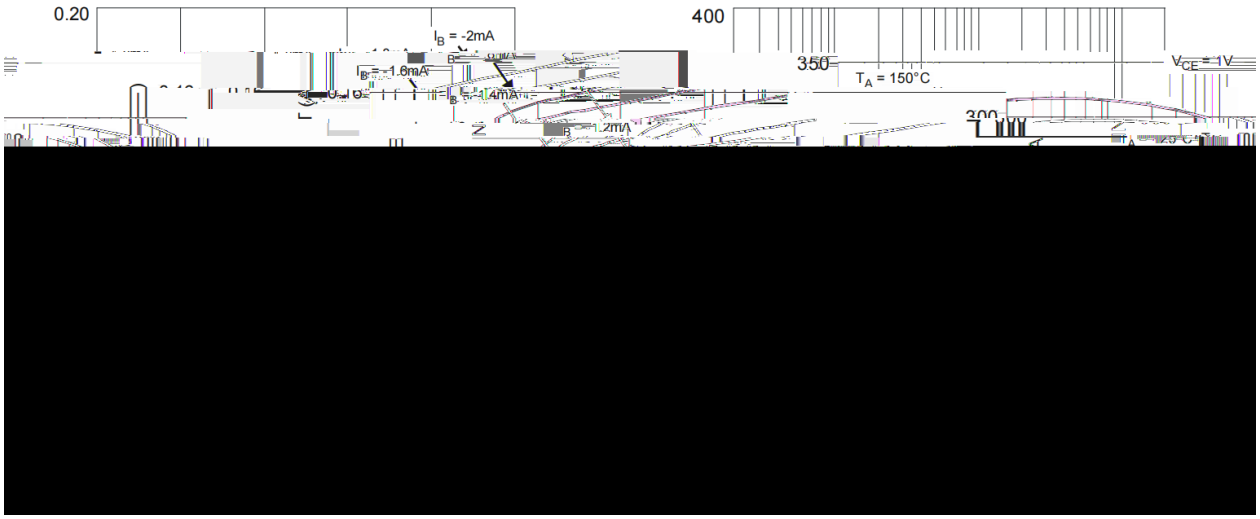


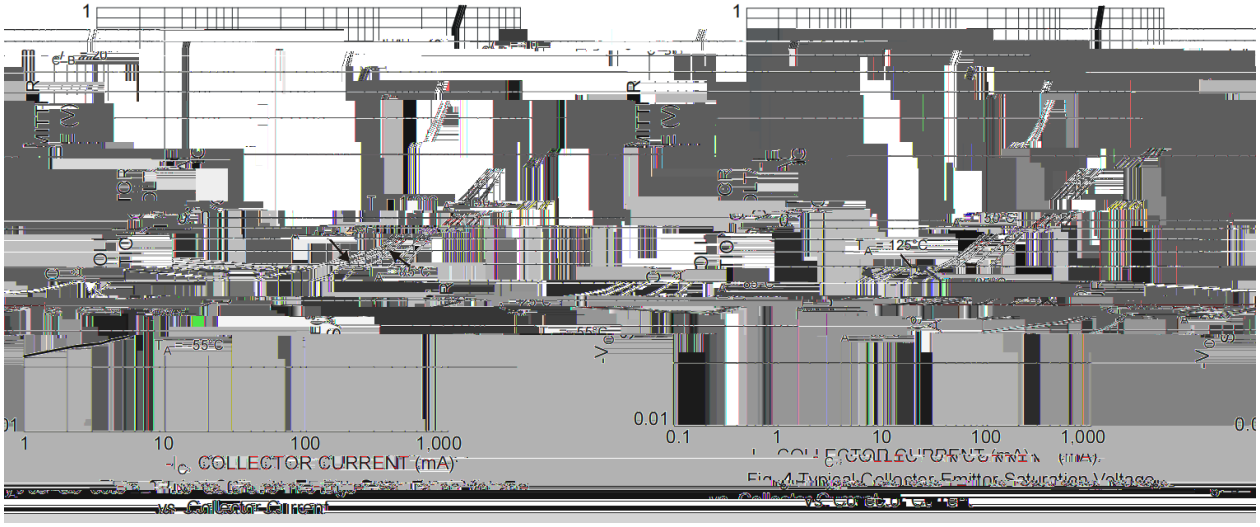
PIN 1 Base PIN 2 Emitter PIN 3 Collector

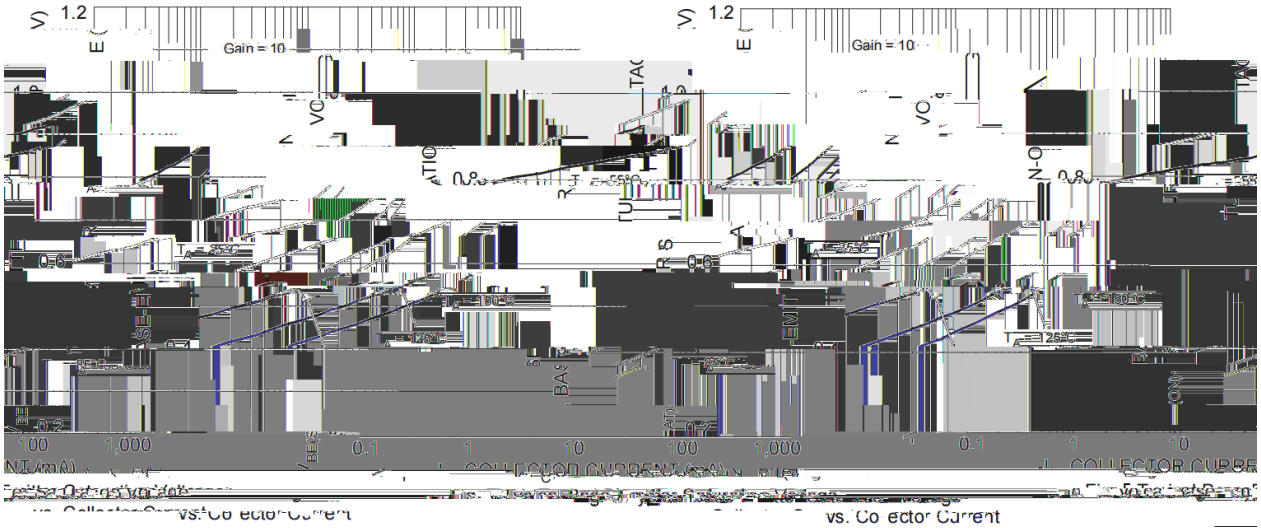
/ h_{FE} Classifications & Marking

h_{FE} Range	100 300
Marking	· H2AK

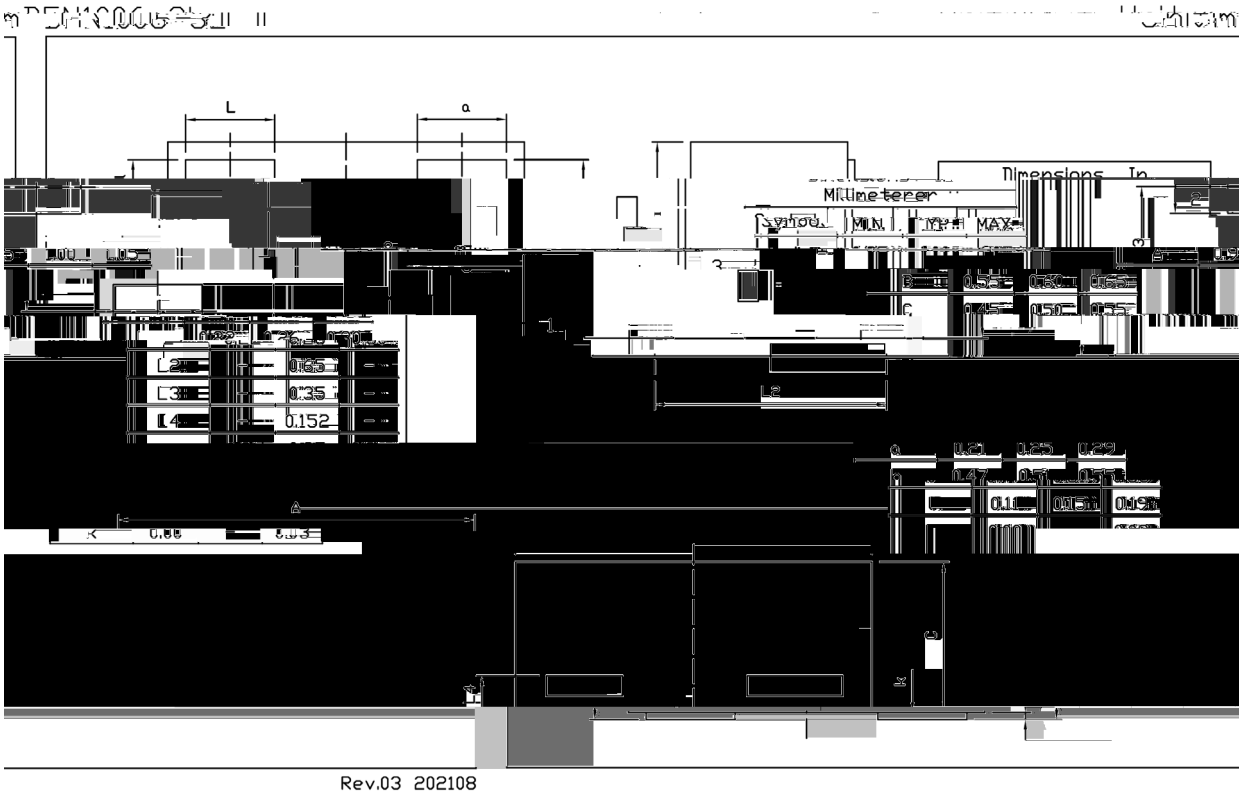
/ Electrical Characteristic Curve



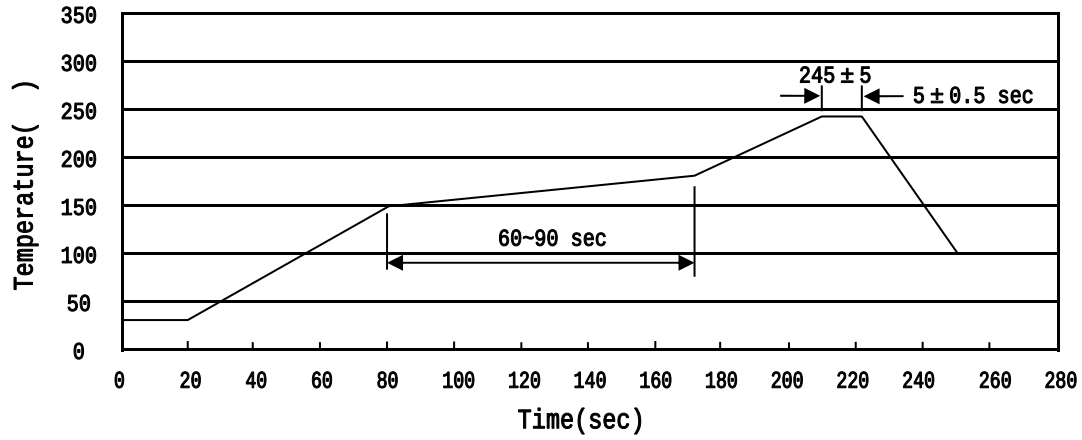




/ Package Dimensions



( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



1	150	180		60	90sec;	1.Preheating:150~180	, Time:60~90sec.
2	245±5				5±0.5sec;	2.Peak Temp.:245±5	, Duration:5±0.5sec.
3			2	10	/sec.	3. Cooling Speed: 2~10	/sec.

Note:

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension		(unit：mm³)
	Units/Reel	Reels/Inner Box /	Units/Inner Box	Inner Boxes/Outer Box /	Units/Outer Box	Reel	Inner Box	Outer Box
DFN1006-3L	10,000	10	100,000	6	600,000	7 ×8	180×120×180	390×385×205

/ Notices